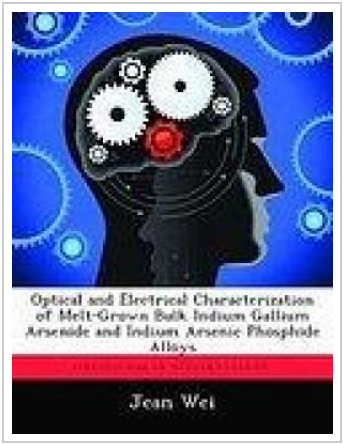

Optical and Electrical Characterization of Melt-Grown Bulk Indium Gallium Arsenide and Indium Arsenic Phosphide Alloys

By Jean Wei

Bibliioscholar Okt 2012, 2012. Taschenbuch. Book Condition: Neu. 246x189x10 mm. This item is printed on demand - Print on Demand Neuware - A new method to determine semiconductor bandgap energy directly from the easily measured transmission spectra was developed. The method was verified using many binary semiconductors with known properties and utilized to determine the unknown ternary semiconductors were determined at various wavelengths and temperatures. Photoluminescence and Hall-effect measurement were performed to identify various electronic transitions, as well as sample quality. The determination of electrical and optical properties of the material will provide important addition to the database of material properties for future optoelectronic device applications. In the near future, newer materials and their applications need to be developed, and often binary and ternary III-V compounds (GaSb, GaP, GaSbP etc.) can be studied using the method developed in this work. 162 pp. Englisch.

Reviews

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